



SI6413DQ-T1-E3 Information



For Reference Only

Part Number SI6413DQ-T1-E3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET P-CH 20V 7.2A 8TSSOP**Package**8-TSSOP (0.173", 4.40mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SI6413DQ-T1-E3 Specifications

Manufacturer Part Number SI6413DQ-T1-E3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-TSSOP (0.173", 4.40mm Width) Series TrenchFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 7.2A (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 800mV @ 400μA Gate Charge (Qg) (Max) @ Vgs 105nC @ 5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 1.05W (Ta) Rds On (Max) @ Id, Vgs 10 mOhm @ 8.8A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-TSSOP Package / Case 8-TSSOP (0.173", 4.40mm Width)		
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C7.2A (Ta)Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id800mV @ 400μAGate Charge (Qg) (Max) @ Vgs105nC @ 5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±8VFET Feature-Power Dissipation (Max)1.05W (Ta)Rds On (Max) @ Id, Vgs10 mOhm @ 8.8A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-TSSOPPackage / Case8-TSSOP (0.173", 4.40mm Width)	Series	TrenchFET?
Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C7.2A (Ta)Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id800mV @ 400μAGate Charge (Qg) (Max) @ Vgs105nC @ 5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±8VFET Feature-Power Dissipation (Max)1.05W (Ta)Rds On (Max) @ Id, Vgs10 mOhm @ 8.8A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-TSSOPPackage / Case8-TSSOP (0.173", 4.40mm Width)	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C7.2A (Ta)Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id800mV @ 400μAGate Charge (Qg) (Max) @ Vgs105nC @ 5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±8VFET Feature-Power Dissipation (Max)1.05W (Ta)Rds On (Max) @ Id, Vgs10 mOhm @ 8.8A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-TSSOPPackage / Case8-TSSOP (0.173", 4.40mm Width)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id800mV @ 400μAGate Charge (Qg) (Max) @ Vgs105nC @ 5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±8VFET Feature-Power Dissipation (Max)1.05W (Ta)Rds On (Max) @ Id, Vgs10 mOhm @ 8.8A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-TSSOPPackage / Case8-TSSOP (0.173", 4.40mm Width)	Drain to Source Voltage (Vdss)	20V
Vgs(th) (Max) @ Id800mV @ 400μAGate Charge (Qg) (Max) @ Vgs105nC @ 5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±8VFET Feature-Power Dissipation (Max)1.05W (Ta)Rds On (Max) @ Id, Vgs10 mOhm @ 8.8A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-TSSOPPackage / Case8-TSSOP (0.173", 4.40mm Width)	Current - Continuous Drain (Id) @ 25°C	7.2A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 105nC @ 5V 105nC @ 5V	Drive Voltage (Max Rds On, Min Rds On)	1.8V, 4.5V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 1.05W (Ta) Rds On (Max) @ Id, Vgs 10 mOhm @ 8.8A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-TSSOP Package / Case 8-TSSOP (0.173", 4.40mm Width)	Vgs(th) (Max) @ Id	800mV @ 400μA
Vgs (Max)±8VFET Feature-Power Dissipation (Max)1.05W (Ta)Rds On (Max) @ Id, Vgs10 mOhm @ 8.8A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-TSSOPPackage / Case8-TSSOP (0.173", 4.40mm Width)	Gate Charge (Qg) (Max) @ Vgs	105nC @ 5V
FET Feature - Comparison (Max) 1.05W (Ta) 1.05W (Ta) Rds On (Max) @ Id, Vgs 10 mOhm @ 8.8A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-TSSOP Package / Case 8-TSSOP (0.173", 4.40mm Width)	Input Capacitance (Ciss) (Max) @ Vds	-
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 mOhm @ 8.8A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-TSSOP Package / Case 8-TSSOP (0.173", 4.40mm Width)	Vgs (Max)	±8V
Rds On (Max) @ Id, Vgs10 mOhm @ 8.8A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-TSSOPPackage / Case8-TSSOP (0.173", 4.40mm Width)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-TSSOP Package / Case 8-TSSOP (0.173", 4.40mm Width)	Power Dissipation (Max)	1.05W (Ta)
Mounting Type Surface Mount Supplier Device Package 8-TSSOP Package / Case 8-TSSOP (0.173", 4.40mm Width)	Rds On (Max) @ Id, Vgs	10 mOhm @ 8.8A, 4.5V
Supplier Device Package 8-TSSOP Package / Case 8-TSSOP (0.173", 4.40mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-TSSOP (0.173", 4.40mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-TSSOP
Report errors?	Package / Case	8-TSSOP (0.173", 4.40mm Width)
		Report errors?

SI6413DQ-T1-E3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SI6413DQ-T1-E3 Payment Methods





















SI6413DQ-T1-E3 Shipping Methods













If you have any question about SI6413DQ-T1-E3, please do not hesitate to contact us!

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